

## Single N-Channel MOSFET

### DESCRIPTION

SMC3332 is the N-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced trench technology devices are well suited for high efficiency fast switching applications, low in-line power loss are needed in small outline surface mount package.

### PART NUMBER INFORMATION

**SMC 3332 S - TR G**  
 a      b      c      d      e

- a : Company name.
- b : Product Serial number.
- c : Package code            S: SOT-23L
- d : Handling code          TR: Tape&Reel
- e : Green produce code G: *RoHS Compliant*

### FEATURES

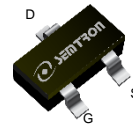
**$V_{DS} = 30V, I_D = 5.6A$**

- $R_{DS(ON)} = 22m\Omega (Typ.) @ V_{GS} = 10V$
- $R_{DS(ON)} = 26m\Omega (Typ.) @ V_{GS} = 4.5V$
- $R_{DS(ON)} = 38m\Omega (Typ.) @ V_{GS} = 2.5V$

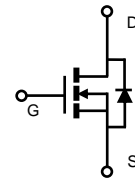
- ◆ Fast switch
- ◆ 2.5V Low gate drive applications

### APPLICATIONS

- ◆ Hand-Held Instruments
- ◆ Load Switch
- ◆ LED Applications



SOT-23L



### ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^\circ C$ Unless otherwise noted)

Symbol	Parameter	Rating	Units
$V_{DSS}$	Drain-Source Voltage	30	V
$V_{GSS}$	Gate-Source Voltage	$\pm 12$	V
$I_D$	Continuous Drain Current	$T_A = 25^\circ C$	5.6
		$T_A = 70^\circ C$	4.5
$I_{DM}$	Pulsed Drain Current <sup>A</sup>	23	A
$I_{AS}$	Avalanche Current <sup>A</sup>	8	A
$E_{AS}$	Single Pulse Avalanche energy $L=0.1mH$ <sup>AD</sup>	3.2	mJ
$P_D$	Power Dissipation <sup>B</sup>	$T_A = 25^\circ C$	1.4
		$T_A = 70^\circ C$	0.9
$T_J$	Operation Junction Temperature	-55/150	$^\circ C$
$T_{STG}$	Storage Temperature Range	-55/150	$^\circ C$

### THERMAL RESISTANCE

Symbol	Parameter	Typ	Max	Units
$R_{\theta JA}$	Thermal Resistance Junction to Ambient <sup>B</sup>	$t \leq 10s$	80	$^\circ C/W$
	Thermal Resistance Junction to Ambient <sup>BC</sup>	Steady-State	120	

## ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ Unless otherwise noted)

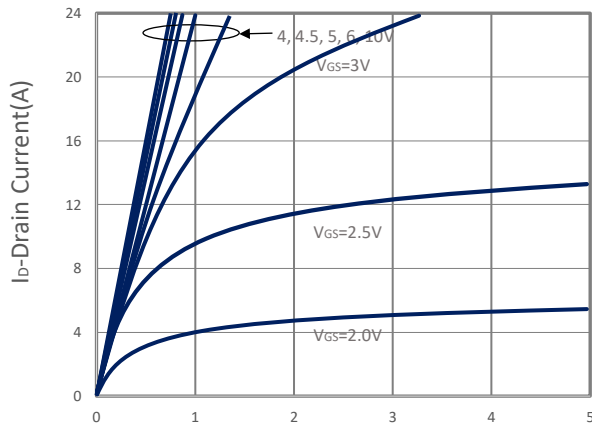
Symbol	Parameter	Condition	Min	Typ	Max	Unit
<b>Static Parameters</b>						
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	30			V
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	0.5	0.7	1	V
I <sub>GSS</sub>	Gate Leakage Current	V <sub>DS</sub> =0V, V <sub>GS</sub> =±12V			±100	nA
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V, T <sub>J</sub> =25°C			1	μA
		V <sub>DS</sub> =24V, V <sub>GS</sub> =0V, T <sub>J</sub> =75°C			10	
R <sub>DS(ON)</sub>	Drain-source On-Resistance	V <sub>GS</sub> =10V, I <sub>D</sub> =5.6A		22	26	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =4.5A		26	32	
		V <sub>GS</sub> =2.5V, I <sub>D</sub> =3.2A		38	48	
G <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =10V, I <sub>D</sub> =3A		7		S
<b>Diode Characteristics</b>						
V <sub>SD</sub>	Diode Forward Voltage	I <sub>S</sub> =1A, V <sub>GS</sub> =0V		0.75	1	V
I <sub>S</sub>	Continuous Source Current				2.8	A
<b>Dynamic and Switching Parameters</b>						
Q <sub>g</sub> (10V)	Total Gate Charge	V <sub>DS</sub> =15V, V <sub>GS</sub> =10V, I <sub>D</sub> =5A		13.5	18.9	nC
Q <sub>g</sub> (4.5V)	Total Gate Charge			6.6	8.9	
Q <sub>gs</sub>	Gate-Source Charge			1.5	3.5	
Q <sub>gd</sub>	Gate-Drain Charge			1.7	2.4	
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =15V, V <sub>GS</sub> =0V, f=1MHz		585		pF
C <sub>oss</sub>	Output Capacitance			42		
C <sub>rss</sub>	Reverse Transfer Capacitance			35		
t <sub>d(on)</sub>	Turn-On Time	V <sub>DD</sub> =15, V <sub>GEN</sub> =10V R <sub>G</sub> =6Ω, I <sub>D</sub> =1A		4.25	8.1	nS
t <sub>r</sub>				15.8	30	
t <sub>d(off)</sub>	Turn-Off Time			31	59	
t <sub>f</sub>				9.2	17	

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged.

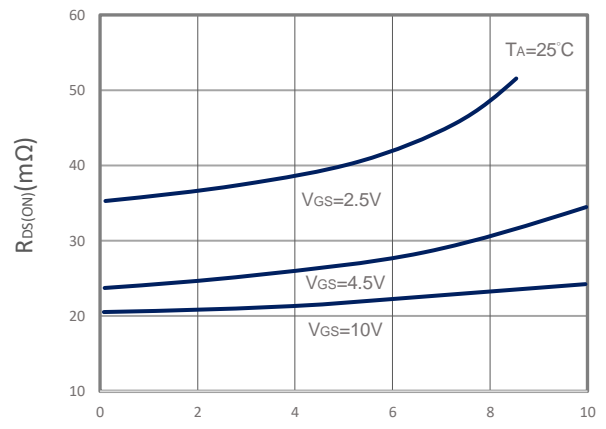
- Pulsed width limited by maximum junction temperature, T<sub>J(MAX)</sub>=150°C.
- The value of R<sub>θJA</sub> is measured with the device mounted on 1in2 FR-4 board in a still air environment with maximum junction temperature T<sub>J(MAX)</sub>=150°C (initial temperature T<sub>A</sub>=25°C).
- T<sub>J(MAX)</sub>=150°C, using junction-to-case thermal resistance (R<sub>θJC</sub>) is more useful in additional heat sinking is used.
- The EAS data shows Max, tested and pulse width limited by T<sub>J(MAX)</sub>=150°C (initial temperature T<sub>J</sub>=25°C).

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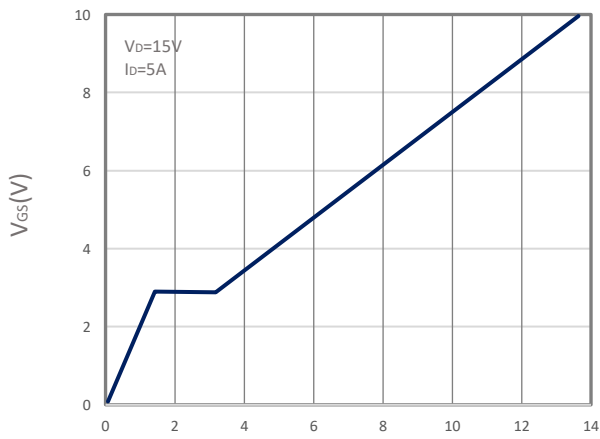
## TYPICAL CHARACTERISTICS



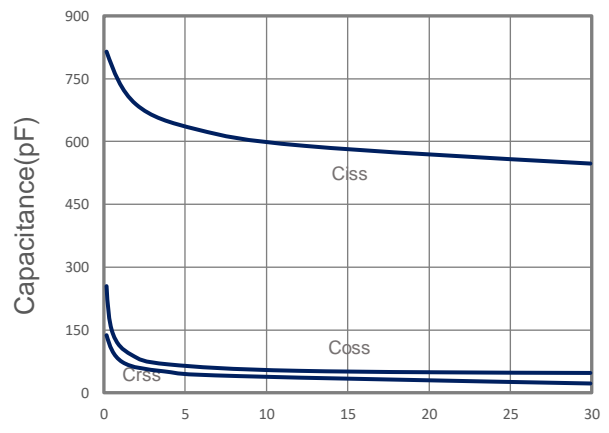
V<sub>DS</sub>-Drain Source Voltage(V)  
Output Characteristics



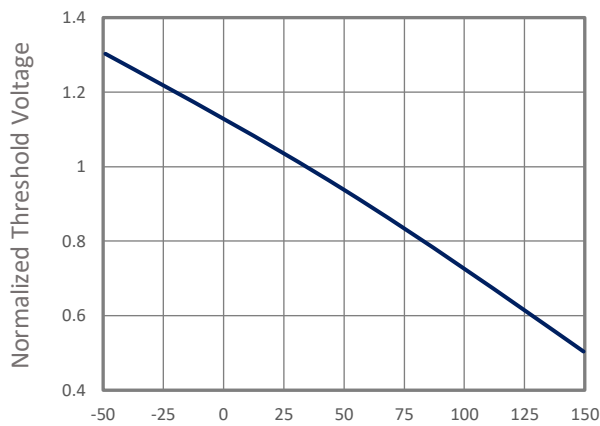
I<sub>D</sub>-Drain Current(A)  
Drain-Source On Resistance



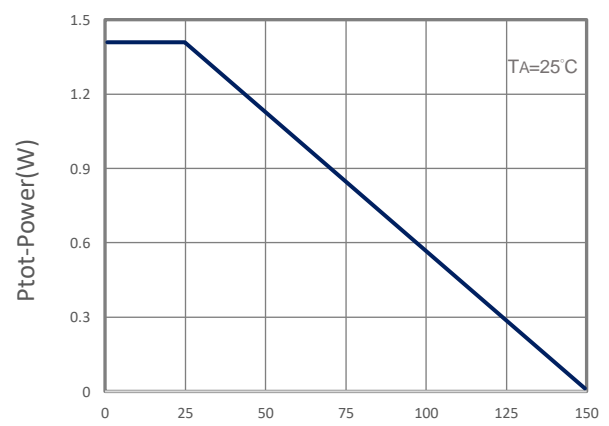
Q<sub>g</sub>-Gate Charge(nC)  
Gate Charge



V<sub>DS</sub>-Drain Source Voltage(V)  
Capacitance

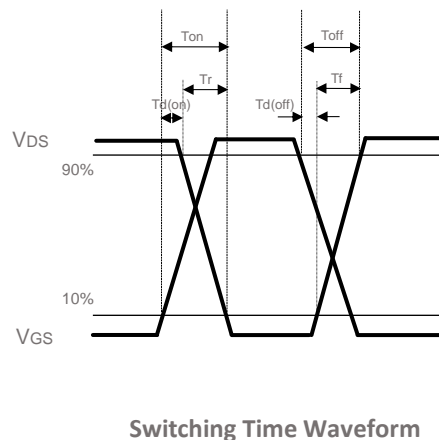
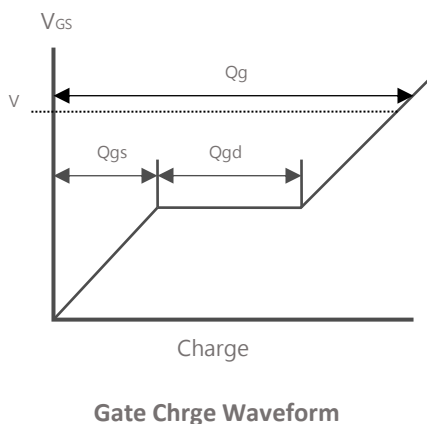
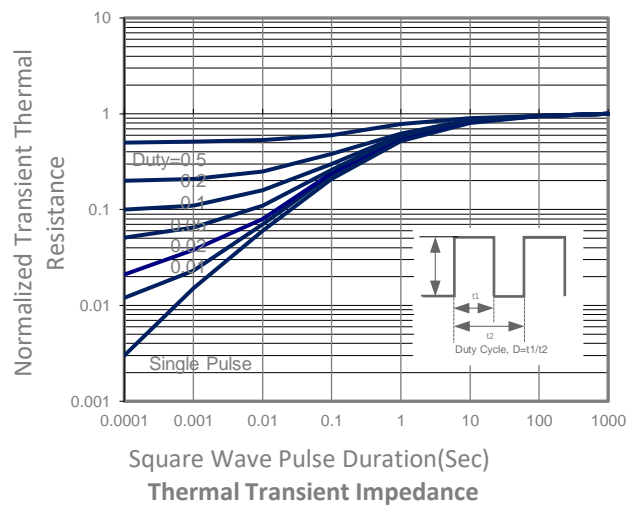
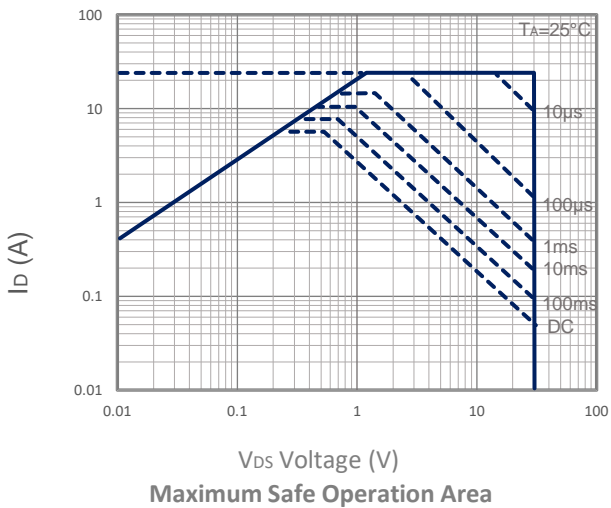
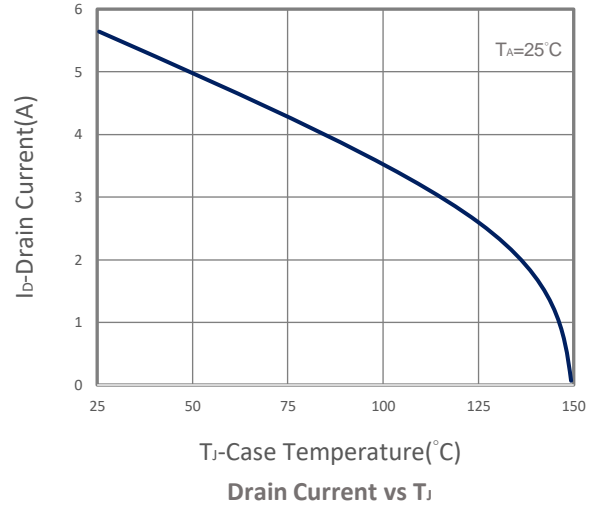
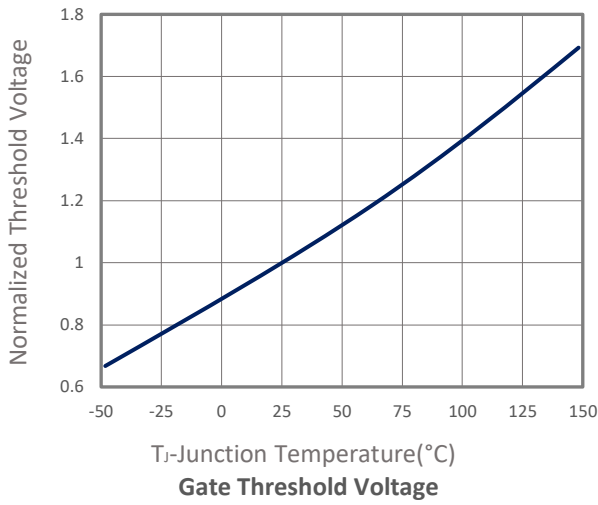


T<sub>J</sub>-Junction Temperature(°C)  
Gate Threshold Voltage

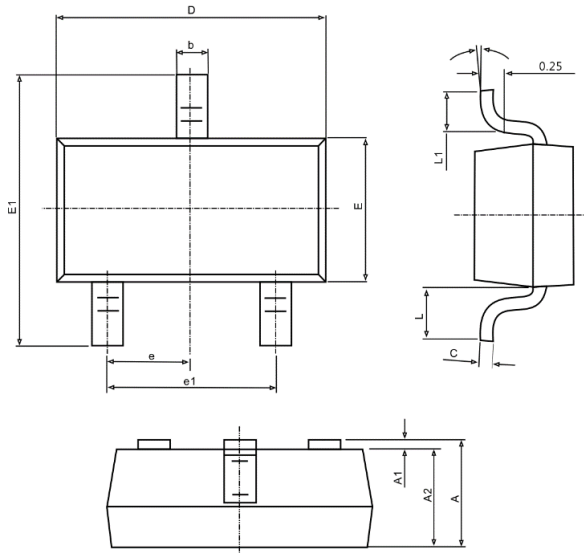


T<sub>A</sub>-Junction Temperature(°C)  
Power Dissipation

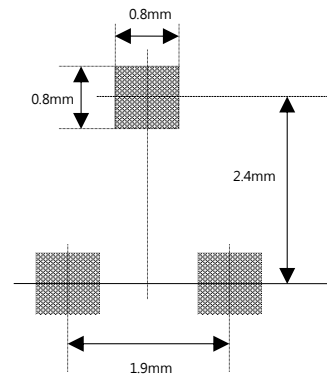
## TYPICAL CHARACTERISTICS



## ■ SOT-23L PACKAGE DIMENSIONS



Recommended Minimum Pad(mm)



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.000	1.300	0.039	0.049
A1	0.000	0.100	0.000	0.004
A2	1.000	1.200	0.039	0.047
b	0.300	0.500	0.012	0.020
c	0.047	0.207	0.002	0.008
D	2.800	3.000	0.110	0.118
E	1.500	1.700	0.059	0.067
E1	2.600	3.000	0.102	0.118
e	0.950 TYP.		0.037 TYP.	
e1	1.900 TYP.		0.075 TYP.	
L1	0.250	0.550	0.010	0.022
θ	0°	8°	0°	8°